

## R-C Thermal Model Parameters

### DESCRIPTION

The parametric values in the R-C thermal model have been derived using curve-fitting techniques. These techniques are described in "[A Simple Method of Generating Thermal Models for a Power MOSFET](#)"[1]. When implemented in P-Spice, these values have matching characteristic curves to the Single Pulse Transient Thermal Impedance curves for the MOSFET.

R-C values for the electrical circuit in the Foster/Tank and Cauer/Filter configurations are included.

*Note:*

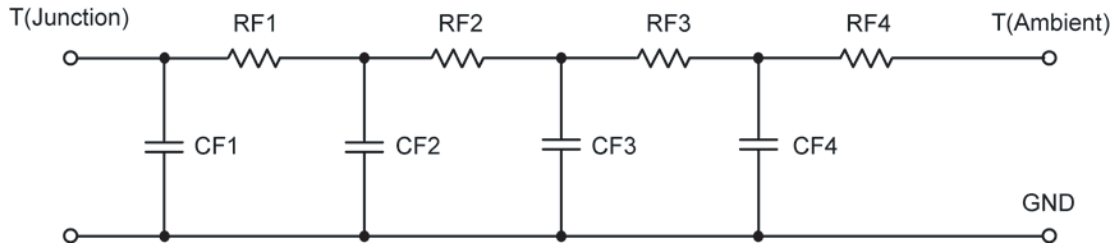
*For a detailed explanation of implementing these values in P-SPICE, refer to [Application Note AN609 Thermal Simulations Of Power MOSFETs on P-SPICE Platform](#).*

### R-C THERMAL MODEL FOR TANK CONFIGURATION



<b>R-C VALUES FOR TANK CONFIGURATION</b>			
Thermal Resistance (°C/W)			
Junction to	Ambient	Case	Foot
RT1	6.4512	N/A	12.8938
RT2	19.7375	N/A	3.6871
RT3	28.1266	N/A	13.3442
RT4	55.6847	N/A	10.0749
Thermal Capacitance (Joules/°C)			
Junction to	Ambient	Case	Foot
CT1	1.2110 m	N/A	140.7837 m
CT2	8.6101 m	N/A	435.8247 u
CT3	53.9851 m	N/A	4.4091 m
CT4	1.2507	N/A	16.4710 m

*This document is intended as a SPICE modeling guideline and does not constitute a commercial product data sheet. Designers should refer to the appropriate data sheet of the same number for guaranteed specification limits.*

**R-C THERMAL MODEL FOR FILTER CONFIGURATION****R-C VALUES FOR FILTER CONFIGURATION**

Thermal Resistance (°C/W)			
Junction to	Ambient	Case	Foot
RF1	7.9351	N/A	4.3869
RF2	23.8402	N/A	17.8937
RF3	25.0868	N/A	7.8069
RF4	53.1379	N/A	9.9125
Thermal Capacitance (Joules/°C)			
Junction to	Ambient	Case	Foot
CF1	986.3980 u	N/A	389.8923 u
CF2	6.2199 m	N/A	2.8419 m
CF3	50.8583 m	N/A	19.1939 m
CF4	1.2517	N/A	160.4153 m

Note: NA indicates not applicable

## Reference:

[1] "A Simple Method of Generating Thermal Models for a Power MOSFET" by Wharton McDaniel and Kandarp Pandya. IEEE / SEMITHERM 2002

